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- Trimmed Offset Voltage: TLC27L9...900 μV Max at 25°C, V<sub>DD</sub> = 5 V
- Input Offset Voltage Drift . . . Typically 0.1 μV/Month, Including the First 30 Days
- Wide Range of Supply Voltages Over Specified Temperature Range: 0°C to 70°C...3 V to 16 V -40°C to 85°C...4 V to 16 V -55°C to 125°C...4 V to 16 V
- Single-Supply Operation
- Common-Mode Input Voltage Range Extends Below the Negative Rail (C-Suffix, I-Suffix Types)
- Ultra-Low Power . . . Typically 195 μW at 25°C, V<sub>DD</sub> = 5 V
- Output Voltage Range includes Negative Rail
- High Input Impedance . . .  $10^{12} \Omega$  Typ
- ESD-Protection Circuitry
- Small-Outline Package Option Also Available in Tape and Reel
- Designed-In Latch-Up Immunity

#### description

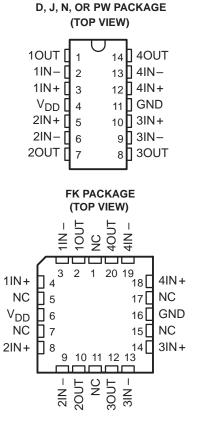
The TLC27L4 and TLC27L9 quad operational amplifiers combine a wide range of input offset voltage grades with low offset voltage drift, high input impedance, extremely low power, and high gain.

These devices use Texas instruments silicon-gate LinCMOS<sup>™</sup> technology, which provides offset voltage stability far exceeding the stability available with conventional metal-gate processes.

The extremely high input impedance, low bias currents, and low-power consumption make these cost-effective devices ideal for high-gain, low- frequency, low-power applications. Four offset voltage grades are available (C-suffix and I-suffix types), ranging from the low-cost TLC27L4 (10 mV) to the high-precision TLC27L9 (900  $\mu$ V). These advantages, in combination with good common-mode rejection and supply voltage rejection, make these devices a good choice for new state-of-the-art designs as well as for upgrading existing designs.

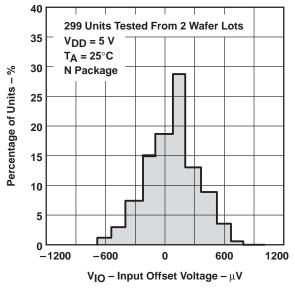
LinCMOS is a trademark of Texas Instruments Incorporated.





NC – No internal connection

#### DISTRIBUTION OF TLC27L9 INPUT OFFSET VOLTAGE



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#### description (continued)

In general, many features associated with bipolar technology are available on LinCMOS<sup>™</sup> operational amplifiers, without the power penalties of bipolar technology. General applications such as transducer interfacing, analog calculations, amplifier blocks, active filters, and signal buffering are easily designed with the TLC27L4 and TLC27L9. The devices also exhibit low voltage single-supply operation and ultra-low power consumption, making them ideally suited for remote and inaccessible battery-powered applications. The common-mode input voltage range includes the negative rail.

A wide range of packaging options is available, including small-outline and chip-carrier versions for high-density system applications.

The device inputs and outputs are designed to withstand –100-mA surge currents without sustaining latch-up.

The TLC27L4 and TLC27L9 incorporate internal ESD-protection circuits that prevent functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.2; however, care should be exercised in handling these devices, as exposure to ESD may result in the degradation of the device parametric performance.

The C-suffix devices are characterized for operation from  $0^{\circ}$ C to  $70^{\circ}$ C. The I-suffix devices are characterized for operation from  $-40^{\circ}$ C to  $85^{\circ}$ C. The M-suffix devices are characterized for operation from  $-55^{\circ}$ C to  $125^{\circ}$ C.

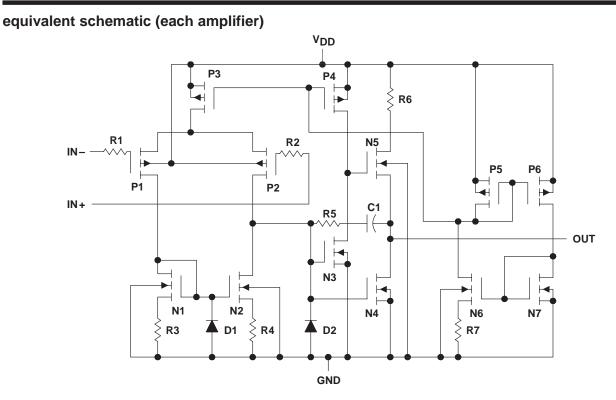
			PA	CKAGED DEVIC	ES		
TA	V <sub>IO</sub> max AT 25°C	SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (J)	PLASTIC DIP (N)	TSSOP (PW)	CHIP FORM (Y)
	900 μV	TLC27L9CD	—	—	TLC27L9CN	—	—
0°C to 70°C	2 mV	TLC27L4BCD	—	—	TLC27L4BCN	—	—
0.01070.0	5 mV	TLC27L4ACD	_	—	TLC27L4ACN	—	—
	10 mV	TLC27L4CD	—	—	TLC27L4CN	TLC27L4CPW	TLC27L4Y
	900 μV	TLC27L9ID	—	—	TLC27L9IN	—	—
-40°C to 85°C	2 mV	TLC27L4BID	—	—	TLC27L4BIN	—	—
-40°C 10 85°C	5 mV	TLC27L4AID	—	—	TLC27L4AIN	—	—
	10 mV	TLC27L4ID	_	—	TLC27L4IN	—	—
-55°C to 125°C	900 μV	TLC27L9MD	TLC27L9MFK	TLC27L9MJ	TLC27L9MN	—	—
-55 C 10 125 C	10 mV	TLC27L4MD	TLC27L4MFK	TLC27L4MJ	TLC27L4MN	—	—

#### AVAILABLE OPTIONS

The D package is available taped and reeled. Add R suffix to the device type (e.g., TLC27L9CDR).



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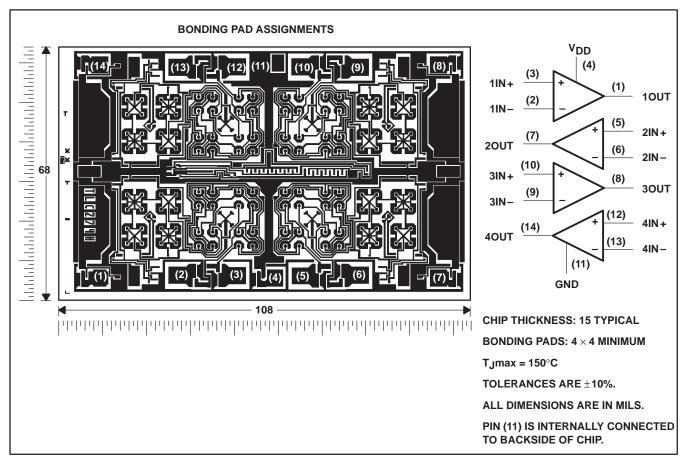




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### TLC27L4Y chip information

These chips, when properly assembled, display characteristics similar to the TLC27L4C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.





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#### absolute maximum ratings over operating free-air temperature (unless otherwise noted)<sup>†</sup>

Differential input voltage, V <sub>ID</sub> (see Input voltage range, V <sub>I</sub> (any input) Input current, I <sub>I</sub> Output current, I <sub>O</sub> (each output) . Total current into V <sub>DD</sub>	Note 2)	$\begin{array}{c} & \pm V_{DD} \\ & -0.3 \text{ V to } V_{DD} \\ & \pm 5 \text{ mA} \\ & & \pm 30 \text{ mA} \\ & & & 45 \text{ mA} \end{array}$
	(or below) 25°C (see Note 3)	
	C suffix	0°C to 70°C
		0°C to 70°C
	C suffix	
Operating free-air temperature, $T_A$	C suffix I suffix M suffix	
Operating free-air temperature, T <sub>A</sub> : Storage temperature range	C suffix	0°C to 70°C 40°C to 85°C 55°C to 125°C 65°C to 150°C
Operating free-air temperature, T <sub>A</sub> Storage temperature range Case temperature for 60 seconds: Lead temperature 1,6 mm (1/16 inc	C suffix I suffix M suffix	0°C to 70°C -40°C to 85°C -55°C to 125°C -65°C to 150°C 260°C W package

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, except differential voltages, are with respect to network ground.

2. Differential voltages are at IN+ with respect to IN-.

3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded (see application section).

		DISSIPATION RA	ATING TABLE		
PACKAGE	$T_A \le 25^{\circ}C$ POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 70°C POWER RATING	T <sub>A</sub> = 85°C POWER RATING	T <sub>A</sub> = 125°C POWER RATING
D	950 mW	7.6 mW/°C	608 mW	494 mW	_
FK	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
J	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
N	1575 mW	12.6 mW/°C	1008 mW	819 mW	—
PW	700 mW	5.6 mW/°C	448 mW	_	—

### DISSIPATION RATING TABLE

#### recommended operating conditions

		C SU	FFIX	I SUI	FFIX	M SU	FFIX	UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Supply voltage, V <sub>DD</sub>		3	16	4	16	4	16	V
	$V_{DD} = 5 V$	-0.2	3.5	-0.2	3.5	0	3.5	V
Common-mode input voltage, VIC	V <sub>DD</sub> = 10 V	-0.2	8.5	-0.2	8.5	0	8.5	v
Operating free-air temperature, $T_A$		0	70	-40	85	-55	125	°C



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### electrical characteristics at specified free-air temperature, V<sub>DD</sub> = 5 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	τ <sub>A</sub> †	ТІ ТІ	_C27L4( _C27L4/ _C27L4E _C27L4E _C27L9(	AC BC	UNIT
						MIN	TYP	MAX	
		TLC27L4C	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		1.1	10	
		TLC27L4C	$R_{S} = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			12	
		TLC27L4AC	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		0.9	5	mV
Vie	Input offset voltage	TLC27L4AC	R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			6.5	
VIO	input onset voltage	TLC27L4BC	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		240	2000	
		120272400	R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			3000	μV
		TLC27L9C	V <sub>O</sub> = 1.4 V,	$V_{IC} = 0,$	25°C		200	900	μv
		12027230	R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			1500	
ανιο	Average temperature co offset voltage	pefficient of input			25°C to 70°C		1.1		μV/°C
	Input offect ourrest (oor	Note ()			25°C		0.1		~^
10	Input offset current (see	e Note 4)	V <sub>O</sub> = 2.5 V,	$V_{IC} = 2.5 V$	70°C		7	300	pА
	Input biog ourrest (see	Nata ()			25°C		0.6		-
IВ	Input bias current (see	Note 4)	V <sub>O</sub> = 2.5 V,	V <sub>IC</sub> = 2.5 V	70°C		40	600	pА
	Common mode input vo	oltage range			25°C	-0.2 to 4	-0.3 to 4.2		V
VICR	(see Note 5)				Full range	-0.2 to 3.5			V
					25°C	3.2	4.1		
Vон	High-level output voltag	e	V <sub>ID</sub> = 100 mV,	$R_L = 1 M\Omega$	0°C	3	4.1		V
					70°C	3	4.2		
					25°C		0	50	
VOL	Low-level output voltage	e	V <sub>ID</sub> = -100 mV,	IOT = 0	0°C		0	50	mV
					70°C		0	50	
					25°C	50	520		
AVD	Large-signal differential amplification	voltage	$V_{O} = 2.5 V \text{ to } 2 V,$	$R_L = 1 M\Omega$	0°C	50	680		V/mV
	ampinoation				70°C	50	380		
					25°C	65	94		
CMRR	Common-mode rejection	n ratio	$V_{IC} = V_{ICR}min$		0°C	60	95		dB
					70°C	60	95		
	Currente under state st				25°C	70	97		
ksvr	Supply-voltage rejection (ΔVDD/ΔVIO)	i ratio	$V_{DD} = 5 V \text{ to } 10 V,$	V <sub>O</sub> = 1.4 V	0°C	60	97		dB
	······································				70°C	60	98		
			V <sub>O</sub> = 2.5 V,		25°C		40	68	
IDD	Supply current (four am	plifiers)	VO = 2.5 V, No load	V <sub>IC</sub> = 2.5 V,	0°C		48	84	μA
					70°C		31	56	

<sup>†</sup> Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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### electrical characteristics at specified free-air temperature, V<sub>DD</sub> = 10 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	T <sub>A</sub> †		.C27L4( .C27L4/ .C27L4E .C27L4E	AC BC	UNIT
						MIN	TYP	MAX	
		TLC27L4C	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		1.1	10	
		12027240	R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			12	mV
		TLC27L4AC	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		0.9	5	IIIV
VIO	Input offset voltage	TLO27L4AC	R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			6.5	
۷IO	input onset voltage	TLC27L4BC	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		260	2000	
		TEO27E4DC	R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			3000	μV
		TLC27L9C	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		210	1200	μv
		12027290	R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			1900	
αVIO	Average temperature co input offset voltage	pefficient of			25°C to 70°C		1		μV/°C
				Х. Б.Х.	25°C		0.1		4
IIO	Input offset current (see	Note 4)	V <sub>O</sub> = 5 V,	VIC = 5 V	70°C		7	300	pА
				Х. Б.Х.	25°C		0.7		4
IВ	Input bias current (see	Note 4)	V <sub>O</sub> = 5 V,	V <sub>IC</sub> = 5 V	70°C		50	600	рA
., <i>,</i>	Common-mode input vo	oltage range			25°C	-0.2 to 9	-0.3 to 9.2		V
VICR	(see Note 5)	0 0			Full range	-0.2 to 8.5			V
					25°C	8	8.9		
Vон	High-level output voltag	e	V <sub>ID</sub> = 100 mV,	$R_L = 1 M\Omega$	0°C	7.8	8.9		V
					70°C	7.8	8.9		
					25°C		0	50	
Vol	Low-level output voltage	е	$V_{ID} = -100 \text{ mV},$	IOT = 0	0°C		0	50	mV
					70°C		0	50	
					25°C	50	870		
Avd	Large-signal differential amplification	voltage	$V_{O} = 1 V \text{ to } 6 V,$	$R_L = 1 M\Omega$	0°C	50	1020		V/mV
	ampinoation				70°C	50	660		
					25°C	65	97		
CMRR	Common-mode rejectio	n ratio	$V_{IC} = V_{ICR}min$		0°C	60	97		dB
					70°C	60	97		
					25°C	70	97		
ksvr	Supply-voltage rejection (ΔVDD/ΔVIO)	n ratio	$V_{DD} = 5 V \text{ to } 10 V,$	V <sub>O</sub> = 1.4 V	0°C	60	97		dB
					70°C	60	98		
					25°C		57	92	
IDD	Supply current (four am	plifiers)	$V_O = 5 V$ , No load	V <sub>IC</sub> = 5 V,	0°C		72	132	μΑ
					70°C		44	80	

<sup>†</sup> Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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### electrical characteristics at specified free-air temperature, V<sub>DD</sub> = 5 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	TAţ	ТІ ТІ	_C27L4I _C27L4 <i>I</i> _C27L4E _C27L9I	AI BI	UNIT
						MIN	TYP	MAX	
		TLC27L4I	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		1.1	10	
		11027141	R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			13	mV
		TLC27L4AI	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		0.9	5	IIIV
VIO	Input offset voltage		R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			7	
٩O	input onset voltage	TLC27L4BI	V <sub>O</sub> = 1.4 V,	$V_{IC} = 0,$	25°C		240	2000	
			R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			3500	μV
		TLC27L9I	V <sub>O</sub> = 1.4 V,	$V_{IC} = 0,$	25°C		200	900	μν
			R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			2000	
αΛΙΟ	Average temperature co offset voltage	pefficient of input			25°C to 85°C		1.1		μV/°C
	Input offect ourrent (co	Note ()			25°C		0.1		~^
10	Input offset current (see	e Note 4)	V <sub>O</sub> = 2.5 V,	V <sub>IC</sub> = 2.5 V	85°C		24	1000	pА
	Input biog ourrent (one	Note ()			25°C		0.6		~^
ΙB	Input bias current (see	Note 4)	V <sub>O</sub> = 2.5 V,	V <sub>IC</sub> = 2.5 V	85°C		200	2000	pА
	Common-mode input v	oltage range			25°C	-0.2 to 4	-0.3 to 4.2		V
VICR	(see Note 5)	0 0			Full range	-0.2 to 3.5			V
					25°C	3.2	4.1		
Vон	High-level output voltage	e	V <sub>ID</sub> = 100 mV,	$R_L = 1 M\Omega$	-40°C	3	4.1		V
					85°C	3	4.2		
					25°C		0	50	
Vol	Low-level output voltag	е	$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	-40°C		0	50	mV
					85°C		0	50	
					25°C	50	480		
AVD	Large-signal differentia amplification	voltage	$V_{O} = 0.25 V \text{ to } 2 V,$	$R_L = 1 M\Omega$	-40°C	50	900		V/mV
	ampinoation				85°C	50	330		
					25°C	65	94		
CMRR	Common-mode rejection	n ratio	$V_{IC} = V_{ICR}min$		-40°C	60	95		dB
					85°C	60	95		
	Complex coltants and a st	, notio			25°C	70	97		
<b>k</b> SVR	Supply-voltage rejection (ΔVDD/ΔVIO)	n ratio	$V_{DD} = 5 V \text{ to } 10 V,$	V <sub>O</sub> = 1.4 V	-40°C	60	97		dB
	······································				85°C	60	98		
					25°C		39	68	
IDD	Supply current (four an	plifiers)	$V_{O} = 2.5 V$ , No load	$V_{IC} = 2.5 V,$	-40°C		62	108	μA
					85°C		29	52	

<sup>†</sup> Full range is  $-40^{\circ}$ C to  $85^{\circ}$ C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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### electrical characteristics at specified free-air temperature, V<sub>DD</sub> = 10 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	TAţ	ТІ ТІ	-C27L4I -C27L4/ -C27L4E -C27L9I	AI 31	UNIT
						MIN	TYP	MAX	
		TLC27L4I	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		1.1	10	
		11027141	$R_{S} = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			13	mV
		TLC27L4AI	V <sub>O</sub> = 1.4 V,	$V_{IC} = 0,$	25°C		0.9	5	IIIV
VIO	Input offset voltage	TLO27L4AI	R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			7	
۷IO	input onset voltage	TLC27L4BI	V <sub>O</sub> = 1.4 V,	$V_{IC} = 0,$	25°C		260	2000	
		160276401	R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			3500	μV
		TLC27L9I	V <sub>O</sub> = 1.4 V,	$V_{IC} = 0,$	25°C		210	1200	μv
		16027691	R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			2900	
ανιο	Average temperature co offset voltage	efficient of input			25°C to 85°C		1		μV/°C
1	lanut effect summert (e.e.s				25°C		0.1		- 0
ΙΟ	Input offset current (see	Note 4)	V <sub>O</sub> = 5 V,	$V_{IC} = 5 V$	85°C		26	1000	pА
l	lanut hing summer (as a h	ata (1)			25°C		0.7		- 0
IВ	Input bias current (see N	ote 4)	V <sub>O</sub> = 5 V,	V <sub>IC</sub> =.5 V	85°C		220	2000	рА
	Common-mode input vo	tage range			25°C	-0.2 to 9	-0.3 to 9.2		V
VICR	(see Note 5)	0 0			Full range	-0.2 to 8.5			V
					25°C	8	8.9		
Vон	High-level output voltage	•	V <sub>ID</sub> = 100 mV,	$R_L = 1 M\Omega$	-40°C	7.8	8.9		V
					85°C	7.8	8.9		
					25°C		0	50	
Vol	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	-40°C		0	50	mV
					85°C		0	50	
					25°C	50	800		
AVD	Large-signal differential amplification	voltage	$V_{O} = 1 V \text{ to } 6 V,$	$R_L = 1 M\Omega$	-40°C	50	1550		V/mV
					85°C	50	585		
					25°C	65	97		
CMRR	Common-mode rejection	ratio	$V_{IC} = V_{ICR}min$		-40°C	60	97		dB
					85°C	60	98		
					25°C	70	97		
ksvr	Supply-voltage rejection $(\Delta V_{DD}/\Delta V_{IO})$	ratio	$V_{DD} = 5 V \text{ to } 10 V,$	V <sub>O</sub> = 1.4 V	-40°C	60	97		dB
					85°C	60	98		
					25°C		57	92	
IDD	Supply current (four amp	lifiers)	$V_{O} = 5 V$ , No load	$V_{IC} = 5 V,$	-40°C		98	172	μA
					85°C		40	72	

<sup>†</sup> Full range is  $-40^{\circ}$ C to  $85^{\circ}$ C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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### electrical characteristics at specified free-air temperature, V<sub>DD</sub> = 5 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	т <sub>А</sub> †		.C27L4N .C27L9N		UNIT
						MIN	TYP	MAX	
			V <sub>O</sub> = 1.4 V,	VIC = 0,	25°C		1.1	10	
Vie	In put offect veltoge	TLC27L4M	R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			12	mV
VIO	Input offset voltage	TLC27L9M	V <sub>O</sub> = 1.4 V,	$V_{IC} = 0,$	25°C		200	900	μV
		16276910	R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			3750	μv
αΛΙΟ	Average temperature coef offset voltage	ficient of input			25°C to 125°C		1.4		μV/°C
	land offersterment (see N	- ( - 1)	N 05V		25°C		0.1		pА
IO II	Input offset current (see N	ote 4)	V <sub>O</sub> = 2.5 V,	VIC = 2.5 V	125°C		1.4	15	nA
	lanut hing summark (and hig	(a. 4)			25°C		0.6		pА
IВ	Input bias current (see No	te 4)	V <sub>O</sub> = 2.5 V,	V <sub>IC</sub> = 2.5 V	125°C		9	35	nA
\/	Common-mode input volta	ige range			25°C	-0.2 to 4	-0.3 to 4.2		V
VICR	(see Note 5)				Full range	-0.2 to 3.5			V
					25°C	3.2	4.1		
VOH	High-level output voltage		V <sub>ID</sub> = 100 mV,	$R_L = 1 M\Omega$	−55°C	3	4.1		V
					125°C	3	4.2		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	−55°C		0	50	mV
					125°C		0	50	
		11			25°C	50	480		
AVD	Large-signal differential vo amplification	litage	$V_{O} = 0.25 V \text{ to } 2 V,$	$R_L = 1 M\Omega$	−55°C	25	950		V/mV
					125°C	25	200		
					25°C	65	94		
CMRR	Common-mode rejection r	atio	$V_{IC} = V_{ICR}min$		-55°C	60	95		dB
					125°C	60	85		
	Supply voltage rejection	tio			25°C	70	97		
ksvr	Supply-voltage rejection ra $(\Delta V_{DD}/\Delta V_{IO})$	110	$V_{DD} = 5 V \text{ to } 10 V,$	V <sub>O</sub> = 1.4 V	−55°C	60	97		dB
					125°C	60	98		
					25°C		39	68	
IDD	Supply current (four ampli	fiers)	V <sub>O</sub> = 2.5 V, No load	vIC = 2.5 V,	−55°C		69	120	μA
					125°C		27	48	

<sup>†</sup> Full range is  $-55^{\circ}$ C to  $125^{\circ}$ C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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### electrical characteristics at specified free-air temperature, V<sub>DD</sub> = 10 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	τ <sub>A</sub> †		LC27L4N LC27L9N		UNIT
				-		MIN	TYP	MAX	
		TLC27L4M	V <sub>O</sub> = 1.4 V,	VIC = 0,	25°C		1.1	10	mV
VIO	Input offset voltage	1 LC27 L4101	R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			12	IIIV
٥I٧	input onset voltage	TLC27L9M	V <sub>O</sub> = 1.4 V,	$V_{IC} = 0,$	25°C		210	1200	μV
		102703101	R <sub>S</sub> = 50 Ω,	$R_L = 1 M\Omega$	Full range			4300	μv
αΛΙΟ	Average temperature coei input offset voltage	fficient of			25°C to 125°C		1.4		μV/°C
lio.	Input offset current (see N	loto (1)	V <sub>O</sub> = 5 V,	VIC = 5 V	25°C		0.1		pА
10	input onset current (see N	10(8 4)	$v_0 = 3 v$ ,	VIC = 5 V	125°C		1.8	15	nA
lin	Input bias current (see No	(A)	V <sub>O</sub> = 5 V,	V <sub>IC</sub> = 5 V	25°C		0.7		pА
IΒ			v0-3 v,		125°C		10	35	nA
Vien	Common-mode input volta	age range			25°C	0 to 9	-0.3 to 9.2		V
VICR	(see Note 5)				Full range	0 to 8.5			V
					25°C	8	8.9		
Vон	High-level output voltage		V <sub>ID</sub> = 100 mV,	$R_L = 1 M\Omega$	−55°C	7.8	8.8		V
					125°C	7.8	9		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	IOT = 0	−55°C		0	50	mV
					125°C		0	50	
	Lorgo signal differential v	altaga			25°C	50	800		
AVD	Large-signal differential vo amplification	Jilage	V <sub>O</sub> = 1 V to 6 V,	$R_L = 1 M\Omega$	−55°C	25	1750		V/mV
					125°C	25	380		
					25°C	65	97		
CMRR	Common-mode rejection	ratio	$V_{IC} = V_{ICR}min$		−55°C	60	97		dB
					125°C	60	91		
	Supply-voltage rejection ra	atio			25°C	70	97		
<b>k</b> SVR	$(\Delta V_{DD}/\Delta V_{IO})$	auo	$V_{DD} = 5 V \text{ to } 10 V,$	$V_{O} = 1.4 V$	−55°C	60	97		dB
					125°C	60	98		
			$V_{O} = 5 V_{,}$	V <sub>IC</sub> = 5 V,	25°C		57	92	
IDD	Supply current (four ampli	ifiers)	VO = 5 V, No load	$V_{\rm IC} = 0 V,$	−55°C		111	192	μA
					125°C		35	60	

<sup>†</sup> Full range is  $-55^{\circ}$ C to  $125^{\circ}$ C.

NOTES: 4. The typical values of input bias current and Input offset current below 5 pA were determined mathematically.



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# electrical characteristics at specified free-air temperature, $V_{DD}$ = 5 V, $T_A$ = 25°C (unless otherwise noted)

	PARAMETER	TEST CON		Т	LC27L4	<i>,</i>	UNIT
	FARAMETER	TEST CONL	DITIONS	MIN	TYP	MAX	UNIT
VIO	Input offset voltage	V <sub>O</sub> = 1.4 V, R <sub>S</sub> = 50 Ω,	$V_{IC} = 0,$ R <sub>L</sub> = 1 M $\Omega$		1.1	10	mV
ανιο	Average temperature coefficient of input offset voltage	$T_A = 25^{\circ}C$ to $70^{\circ}C$			1.1		μV/°C
lio	Input offset current (see Note 4)	V <sub>O</sub> = 2.5 V,	V <sub>IC</sub> = 2.5 V		0.1		pА
I <sub>IB</sub>	Input bias current (see Note 4)	V <sub>O</sub> = 2.5 V,	V <sub>IC</sub> = 2.5 V		0.6		pА
VICR	Common-mode input voltage range (see Note 5)			-0.2 to 4	-0.3 to 4.2		V
∨он	High-level output voltage	V <sub>ID</sub> = 100 mV,	$R_L = 1 M\Omega$	3.2	4.1		V
VOL	Low-level output voltage	V <sub>ID</sub> = -100 mV,	$I_{OL} = 0$		0	50	mV
AVD	Large-signal differential voltage amplification	$V_{O} = 0.25 V \text{ to } 2 V,$	$R_L = 1 M\Omega$	50	520		V/mV
CMRR	Common-mode rejection ratio	V <sub>IC</sub> = V <sub>ICR</sub> min		65	94		dB
k <sub>SVR</sub>	Supply-voltage rejection ratio ( $\Delta V_{DD} / \Delta V_{IO}$ )	V <sub>DD</sub> = 5 V to 10 V,	V <sub>O</sub> = 1.4 V	70	97		dB
IDD	Supply current (four amplifiers)	V <sub>O</sub> = 2.5 V, No load	V <sub>IC</sub> = 2.5 V,		40	68	μA

# electrical characteristics at specified free-air temperature, $V_{DD}$ = 10 V, $T_A$ = 25 $^\circ C$ (unless otherwise noted)

	PARAMETER	TEST CON		Т	LC27L4	(	UNIT
	PARAMETER	TESTCON	DITIONS	MIN	TYP	MAX	UNIT
VIO	Input offset voltage	$V_{O} = 1.4 V,$ R <sub>S</sub> = 50 $\Omega$ ,	$V_{IC} = 0,$ R <sub>L</sub> = 1 M $\Omega$		1.1	10	mV
αγιο	Average temperature coefficient of input offset voltage	$T_A = 25^{\circ}C$ to $70^{\circ}C$			1		μV/°C
IIO	Input offset current (see Note 4)	V <sub>O</sub> = 5 V,	$V_{IC} = 5 V$		0.1		pА
I <sub>IB</sub>	Input bias current (see Note 4)	V <sub>O</sub> = 5 V,	$V_{IC} = 5 V$		0.7		pА
VICR	Common-mode input voltage range (see Note 5)			-0.2 to 9	-0.3 to 9.2		V
VOH	High-level output voltage	V <sub>ID</sub> = 100 mV,	$R_L = 1 M\Omega$	8	8.9		V
VOL	Low-level output voltage	V <sub>ID</sub> = -100 mV,	IOT = 0		0	50	mV
AVD	Large-signal differential voltage amplification	$V_{O} = 1 V \text{ to } 6 V,$	$R_L = 1 M\Omega$	50	870		V/mV
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}min$		65	97		dB
k <sub>SVR</sub>	Supply-voltage rejection ratio $(\Delta V_{DD}/\Delta V_{IO})$	$V_{DD} = 5 V \text{ to } 10 V,$	V <sub>O</sub> = 1.4 V	70	97		dB
IDD	Supply current (four amplifiers)	V <sub>O</sub> = 5 V, No load	V <sub>IC</sub> = 5 V,		57	92	μA

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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	PARAMETER	TEST CO	ONDITIONS	т <sub>А</sub>	TLC27L4C TLC27L4AC TLC27L4BC TLC27L9C			UNIT	
					MIN	TYP	MAX		
				25°C		0.03			
			VIPP = 1 V	0°C		0.04		]	
SR	Claurente et units gein	$R_L = 1 M\Omega$ ,		70°C		0.03			
SK	Slew rate at unity gain	CL = 20 pF, See Figure 1		25°C	25°C 0.03			V/μs	
		gere i	V <sub>IPP</sub> = 2.5 V	0°C		0.03			
				70°C		0.02		1	
Vn	Equivalent input noise voltage	f = 1 kHZ, See Figure 2	R <sub>S</sub> = 20 Ω,	25°C		70		nV/√Hz	
				25°C		5			
Вом	Maximum output-swing bandwidth		C <sub>L</sub> = 20 pF, See Figure 1	0°C		6		kHz	
			Gee l'igure i	70°C		4.5		1	
				25°C		85			
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	C <sub>L</sub> = 20 pF,	0°C		100		kHz	
				70°C		65		1	
			<i>.</i>	25°C		34°			
φm	Phase margin	V <sub>I</sub> = 10 mV, C <sub>L</sub> = 20 pF,	f = B <sub>1</sub> , See Figure 3	0°C		36°		1	
			coor iguio o	70°C		30°		1	

### operating characteristics at specified free-air temperature, $V_{DD}$ = 5 V

### operating characteristics at specified free-air temperature, $V_{DD} = 10 V$

	PARAMETER	TEST CO	NDITIONS	T <sub>A</sub>	TLC27L4C TLC27L4AC TLC27L4BC TLC27L9C			UNIT
					MIN	TYP	MAX	
				25°C		0.05		
			$V_{IPP} = 1 V$	0°C		0.05		
SR	Slew rate at unity gain	$R_L = 1 M\Omega$ ,		70°C		0.04		V/uo
J SK	Siew rate at unity gain	C <sub>L</sub> = 20 pF, See Figure 1		25°C		0.04		V/μs
			V <sub>IPP</sub> = 5.5 V	0°C	0.05			1
				70°C		0.04		1
Vn	Equivalent input noise voltage	f = 1 kHz <sub>,</sub> See Figure 2	R <sub>S</sub> = 20 Ω,	25°C		70		nV/√Hz
				25°C		1		
ВОМ	Maximum output-swing bandwidth	$V_{O} = V_{OH},$ R <sub>L</sub> = 1 M $\Omega$ ,	C <sub>L</sub> = 20 pF, See Figure 1	0°C		1.3		kHz
		$ X_{L} - 1 $ $ V  \leq 2$ ,	See ligure i	70°C		0.9		
				25°C		110		
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	C <sub>L</sub> = 20 pF,	0°C		125		kHz
		loce rigare e		70°C		90		
			( )	25°C		38°		
∮m	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{I} = 20 \text{ pF},$	f = B <sub>1</sub> , See Figure 3	0°C		40°		
		0L - 20 pr,	eee rigure e	70°C		34°		



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### operating characteristics at specified free-air temperature, $V_{DD}$ = 5 V

	PARAMETER	TEST CO	NDITIONS	TA	TLC27L4I TLC27L4AI TLC27L4BI TLC27L9I			UNIT
			1	25°C	MIN	<b>TYP</b> 0.03	MAX	
			VIPP = 1 V	-40°C		0.03		
		$R_L = 1 M\Omega$ ,		_40 C 85°C		0.04		
SR	Slew rate at unity gain	$C_{L}^{-} = 20 \text{ pF},$		25°C		0.03		V/µs
		See Figure 1	VIPP = 2.5 V	-40°C		0.03		
			1 IFF = 2.0 1	85°C		0.02		
Vn	Equivalent input noise voltage	f = 1 HZ, See Figure 2	R <sub>S</sub> = 20 Ω,	25°C		70		nV/√ <del>Hz</del>
				25°C		5		
Вом	Maximum output-swing bandwidth	$V_{O} = V_{OH},$ R <sub>L</sub> = 1 M $\Omega$ ,	$C_L = 20 \text{ pF},$	-40°C		7		kHz
		$R_{L} = 1 \text{ IVIS2},$	See Figure 1	85°C		4		
				25°C		85		
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	C <sub>L</sub> = 20 pF,	-40°C		130		kHz
		See Figure 3		85°C		55		
	∳m Phase margin	10 - 11	( )	25°C		34°		
φm		$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B <sub>1</sub> , See Figure 3	-40°C		38°		
				85°C		28°		

### operating characteristics at specified free-air temperature, $V_{DD}$ = 10 V

	PARAMETER	TEST CO	NDITIONS	T <sub>A</sub>	T T T T	UNIT		
					MIN	TYP	MAX	
				25°C		0.05		
			$V_{IPP} = 1 V$	-40°C		0.06		
SR	Slew rate at unity gain	R <sub>L</sub> = 1 MΩ, C <sub>L</sub> = 20 pF,		85°C		0.03		V/µs
SK	Siew rate at unity gain	See Figure 1		25°C		0.04		v/µs
			VIPP = 2.5 V	-40°C		0.05		
				85°C		0.03		
V <sub>n</sub>	Equivalent input noise voltage	f = 1 HZ, See Figure 2	R <sub>S</sub> = 20 Ω,	25°C		70		nV/√Hz
		1		25°C		1		
ВОМ	Maximum output-swing bandwidth	$V_{O} = V_{OH},$ R <sub>L</sub> = 1 M $\Omega$ ,	C <sub>L</sub> = 20 pF, See Figure 1	-40°C		1.4		kHz
		$R_{L} = 1 \text{ IVIS2},$	See Figure 1	85°C		0.8		
				25°C		110		
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	C <sub>L</sub> = 20 pF,	-40°C		155		kHz
		Occ riguie 3		85°C		80		1
				25°C		38°		
φm	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B <sub>1</sub> , See Figure 3	-40°C		42°		1
		0 <u> </u>	CCC Figure 5	85°C		32°		



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	PARAMETER	TEST CO	NDITIONS	ТА	T T	UNIT		
					MIN	TYP	MAX	
				25°C		0.03		
			V <sub>IPP</sub> = 1 V	−55°C		0.04		
SR	Clow rate at unity agin	$R_L = 1 M\Omega$ ,		125°C		0.02		1/////
SK	Slew rate at unity gain	CL = 20 pF, See Figure 1		25°C		0.03		V/µs
			VIPP = 2.5 V	−55°C		0.04		
				125°C		0.02		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	R <sub>S</sub> = 20 Ω,	25°C		70		nV/√Hz
				25°C		5		
Вом	Maximum output-swing bandwidth	$V_{O} = V_{OH},$ R <sub>L</sub> = 1 M $\Omega$ ,	C <sub>L</sub> = 20 pF, See Figure 1	−55°C		8		kHz
			occ rigare r	125°C		3		1
			0 00 5	25°C		85		
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	C <sub>L</sub> = 20 pF,	−55°C		140		kHz
				125°C		45		
		10	<u> </u>	25°C		34°		
φm	Phase margin	V <sub>I</sub> = 10 mV, C <sub>L</sub> = 20 pF,	f = B <sub>1</sub> , See Figure 3	−55°C		39°		
				125°C		25°		

### operating characteristics at specified free-air temperature, $V_{DD}$ = 5 V

# operating characteristics at specified free-air temperature, $V_{DD} = 10 V$

	PARAMETER	TEST CO	NDITIONS	тд	TLC27L4M TLC27L9M			UNIT
				~	MIN	TYP	MAX	
				25°C		0.05		
			V <sub>IPP</sub> = 1 V	−55°C		0.06		
SR	Clow rate at unity gain	$R_L = 1 M\Omega$ ,		125°C		0.03		\//uo
J SR	Slew rate at unity gain	C <sub>L</sub> = 20 pF, See Figure 1		25°C		0.04		V/μs
		J 3.	V <sub>IPP</sub> = 5.5 V	−55°C		0.06		
				125°C		0.03		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	R <sub>S</sub> = 20 Ω,	25°C		70		nV/√ <del>Hz</del>
				25°C		1		
ВОМ	Maximum output-swing bandwidth	$V_{O} = V_{OH},$ R <sub>L</sub> = 1 M $\Omega$ ,	CL = 20 pF, See Figure 1	−55°C		1.5		kHz
		1 ( <u></u> 1 1 1 1 1 2 ,	occ rigare r	125°C		0.7		
			· · · ·	25°C		110		
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	C <sub>L</sub> = 20 pF,	−55°C		165		kHz
		Occ rigure 3		125°C		70		
		10 m)(	4 D	25°C		38°		
∮m	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$		−55°C		43°		
		• •,	gui e e	125°C		29°		



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# operating characteristics, $V_{DD} = 5 V$ , $T_A = 25^{\circ}C$

	PARAMETER	TEST CO	NDITIONS	TL	.C27L4Y	'	UNIT
	PARAMETER	TEST CO	MIN	TYP	MAX	UNIT	
SR	Slew rate at unity gain	$R_L = 1 M\Omega,$ $C_I = 20 pF,$	V <sub>IPP</sub> = 1 V		0.03		V/µs
SK	Siew rate at unity gain	See Figure 1	V <sub>IPP</sub> = 2.5 V		0.03		v/μs
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$ ,		70		nV/√Hz
вом	Maximum output-swing bandwidth	$V_{O} = V_{OH},$ R <sub>L</sub> = 1 M $\Omega$ ,	C <sub>L</sub> = 20 pF, See Figure 1		5		kHz
В <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	C <sub>L</sub> = 20 pF,		85		kHz
<sup>¢</sup> m	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B <sub>1</sub> , See Figure 3		34°		

### operating characteristics, $V_{DD}$ = 10 V, $T_A$ = 25°C

	PARAMETER	TEST CO	NDITIONS	TL	.C27L4Y	<b>'</b>	UNIT
	FARAIWETER	TEST CO	NDITIONS	MIN	TYP	MAX	UNIT
SR	Slew rate at unity gain	$R_L = 1 M\Omega$ , $C_I = 20 pF$ ,	V <sub>IPP</sub> = 1 V		0.05		V/µs
- Six	Siew rate at unity gain	See Figure 1	V <sub>IPP</sub> = 5.5 V		0.04		ν/μ5
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	R <sub>S</sub> = 20 Ω,		70		nV/√Hz
BOM	Maximum output-swing bandwidth	$V_{O} = V_{OH},$ R <sub>L</sub> = 1 M $\Omega$ ,	C <sub>L</sub> = 20 pF, See Figure 1		1		kHz
В <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	C <sub>L</sub> = 20 pF,		110		kHz
<sup>¢</sup> m	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B <sub>1</sub> , See Figure 3		38°		

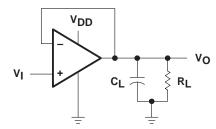


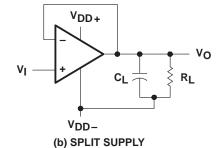
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### PARAMETER MEASUREMENT INFORMATION

#### single-supply versus split-supply test circuits

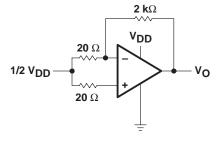
Because the TLC27L4 and TLC27L9 are optimized for single-supply operation, circuit configurations used for the various tests often present some inconvenience since the input signal, in many cases, must be offset from ground. This inconvenience can be avoided by testing the device with split supplies and the output load tied to the negative rail. A comparison of single-supply versus split-supply test circuits is shown below. The use of either circuit gives the same result.

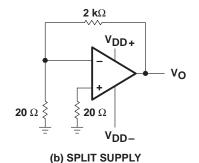




(a) SINGLE SUPPLY

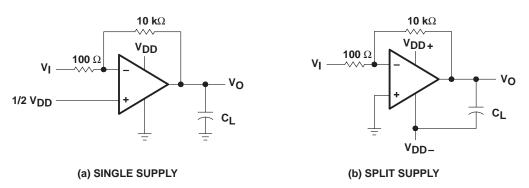






(a) SINGLE SUPPLY

Figure 2. Noise-Test Circuit







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### PARAMETER MEASUREMENT INFORMATION

#### input bias current

Because of the high input impedance of the TLC27L4 and TLC27L9 operational amplifiers, attempts to measure the input bias current can result in erroneous readings. The bias current at normal room ambient temperature is typically less than 1 pA, a value that is easily exceeded by leakages on the test socket. Two suggestions are offered to avoid erroneous measurements:

- 1. Isolate the device from other potential leakage sources. Use a grounded shield around and between the device inputs (see Figure 4). Leakages that would otherwise flow to the inputs are shunted away.
- 2. Compensate for the leakage of the test socket by actually performing an input bias current test (using a picoammeter) with no device in the test socket. The actual input bias current can then be calculated by subtracting the open-socket leakage readings from the readings obtained with a device in the test socket.

One word of caution: many automatic testers as well as some bench-top operational amplifier testers use the servo-loop technique with a resistor in series with the device input to measure the input bias current (the voltage drop across the series resistor is measured and the bias current is calculated). This method requires that a device be inserted into the test socket to obtain a correct reading; therefore, an open-socket reading is not feasible using this method.

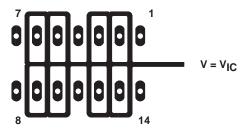


Figure 4. Isolation Metal Around Device Inputs (J and N packages)

#### low-level output voltage

To obtain low-supply-voltage operation, some compromise was necessary in the input stage. This compromise results in the device low-level output being dependent on both the common-mode input voltage level as well as the differential input voltage level. When attempting to correlate low-level output readings with those quoted in the electrical specifications, these two conditions should be observed. If conditions other than these are to be used, please refer to Figures 14 through 19 in the Typical Characteristics of this data sheet.

#### input offset voltage temperature coefficient

Erroneous readings often result from attempts to measure temperature coefficient of input offset voltage. This parameter is actually a calculation using input offset voltage measurements obtained at two different temperatures. When one (or both) of the temperatures is below freezing, moisture can collect on both the device and the test socket. This moisture results in leakage and contact resistance, which can cause erroneous input offset voltage readings. The isolation techniques previously mentioned have no effect on the leakage since the moisture also covers the isolation metal itself, thereby rendering it useless. It is suggested that these measurements be performed at temperatures above freezing to minimize error.



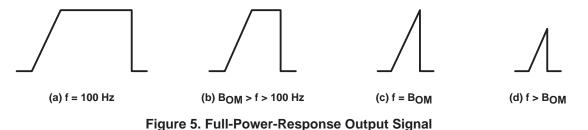
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### PARAMETER MEASUREMENT INFORMATION

#### full-power response

Full-power response, the frequency above which the operational amplifier slew rate limits the output voltage swing, is often specified two ways: full-linear response and full-peak response. The full-linear response is generally measured by monitoring the distortion level of the output while increasing the frequency of a sinusoidal input signal until the maximum frequency is found above which the output contains significant distortion. The full-peak response is defined as the maximum output frequency, without regard to distortion, above which full peak-to-peak output swing cannot be maintained.

Because there is no industry-wide accepted value for significant distortion, the full-peak response is specified in this data sheet and is measured using the circuit of Figure 1. The initial setup involves the use of a sinusoidal input to determine the maximum peak-to-peak output of the device (the amplitude of the sinusoidal wave is increased until clipping occurs). The sinusoidal wave is then replaced with a square wave of the same amplitude. The frequency is then increased until the maximum peak-to-peak output can no longer be maintained (Figure 5). A square wave is used to allow a more accurate determination of the point at which the maximum peak-to-peak output is reached.



#### test time

Inadequate test time is a frequent problem, especially when testing CMOS devices in a high-volume, short-test-time environment. Internal capacitances are inherently higher in CMOS than in bipolar and BiFET devices and require longer test times than their bipolar and BiFET counterparts. The problem becomes more pronounced with reduced supply levels and lower temperatures.



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### **TYPICAL CHARACTERISTICS**

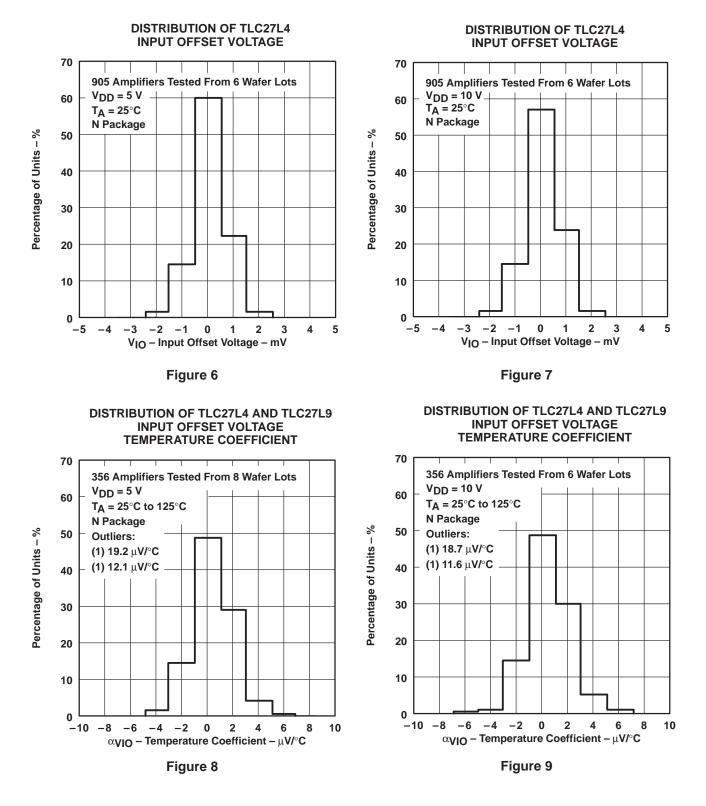
			FIGURE
VIO	Input offset voltage	Distribution	6, 7
αVIO	Temperature coefficient	Distribution	8, 9
VOH	High-level output voltage	vs High-level output current vs Supply voltage vs Free-air temperature	10, 11 12 13
V <sub>OL</sub>	Low-level output voltage	vs Common-mode input voltage vs Differential input voltage vs Free-air temperature vs Low-level output current	14, 15 16 17 18, 19
AVD	Differential voltage amplification	vs Supply voltage vs Free-air temperature vs Frequency	20 21 32, 33
IIB/IIO	Input bias and input offset current	vs Free-air temperature	22
VIC	Common-mode input voltage	vs Supply voltage	23
IDD	Supply current	vs Supply voltage vs Free-air temperature	24 25
SR	Slew rate	vs Supply voltage vs Free-air temperature	26 27
	Normalized slew rate	vs Free-air temperature	28
V <sub>O(PP)</sub>	Maximum peak-to-peak output voltage	vs Frequency	29
B <sub>1</sub>	Unity-gain bandwidth	vs Free-air temperature vs Supply voltage	30 31
<sup>¢</sup> m	Phase margin	vs Supply voltage vs Free-air temperature vs Capacitive loads	34 35 36
Vn	Equivalent input noise voltage	vs Frequency	37
φ	Phase shift	vs Frequency	32, 33

#### Table of Graphs



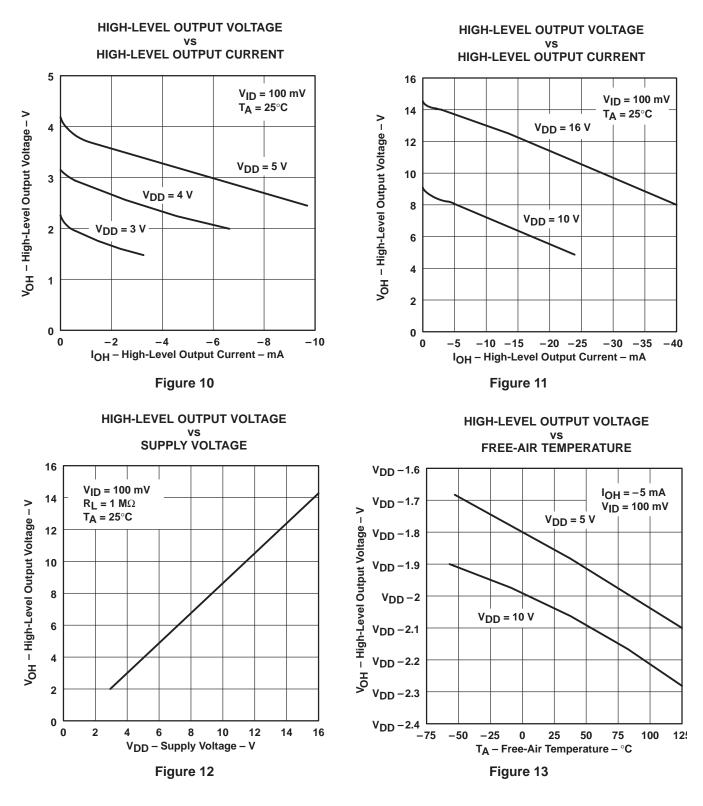
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#### **TYPICAL CHARACTERISTICS**





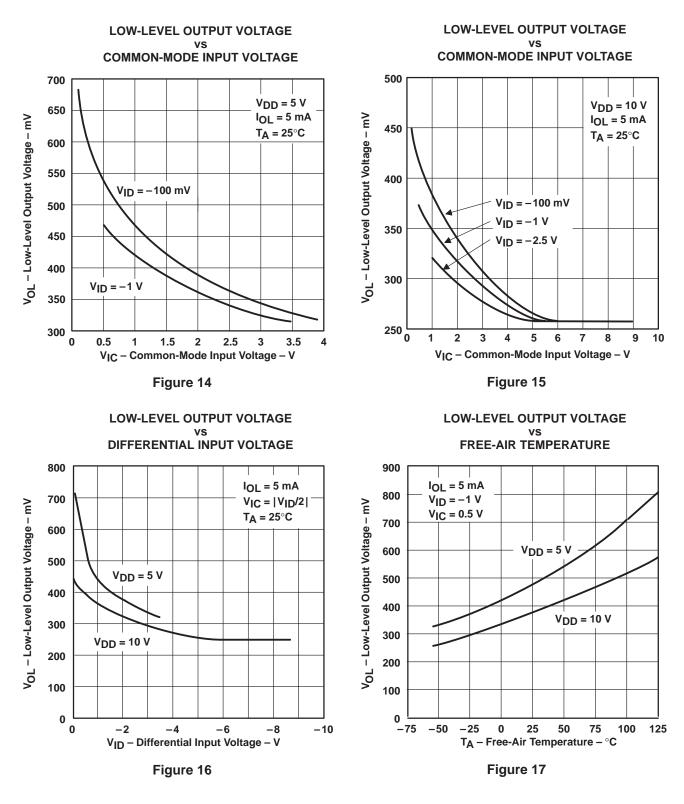
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TYPICAL CHARACTERISTICS<sup>†</sup>



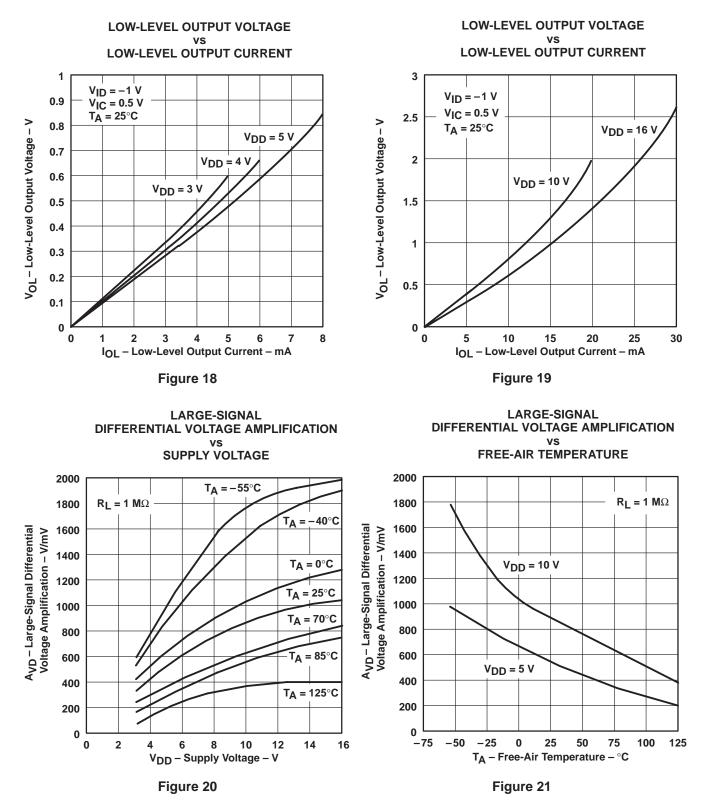
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#### **TYPICAL CHARACTERISTICS<sup>†</sup>**



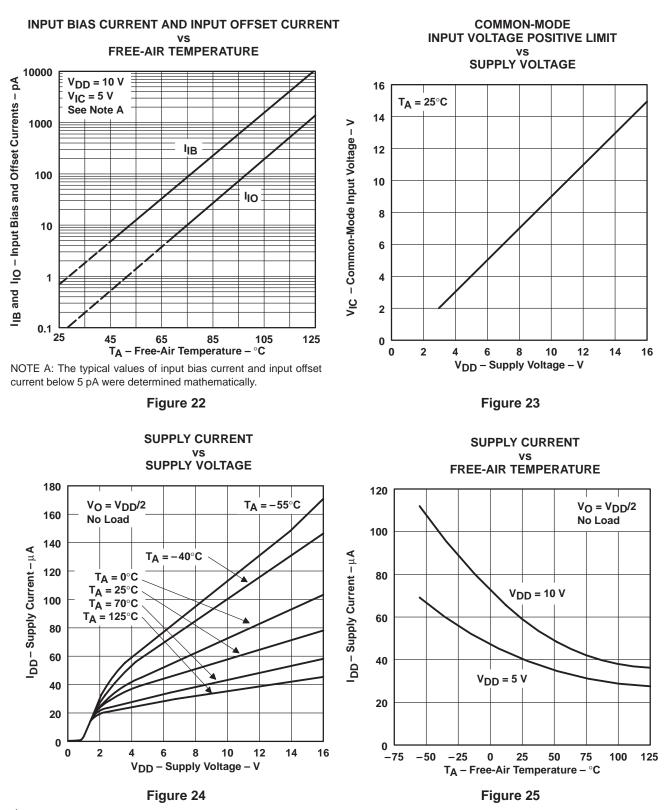
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**TYPICAL CHARACTERISTICS<sup>†</sup>** 



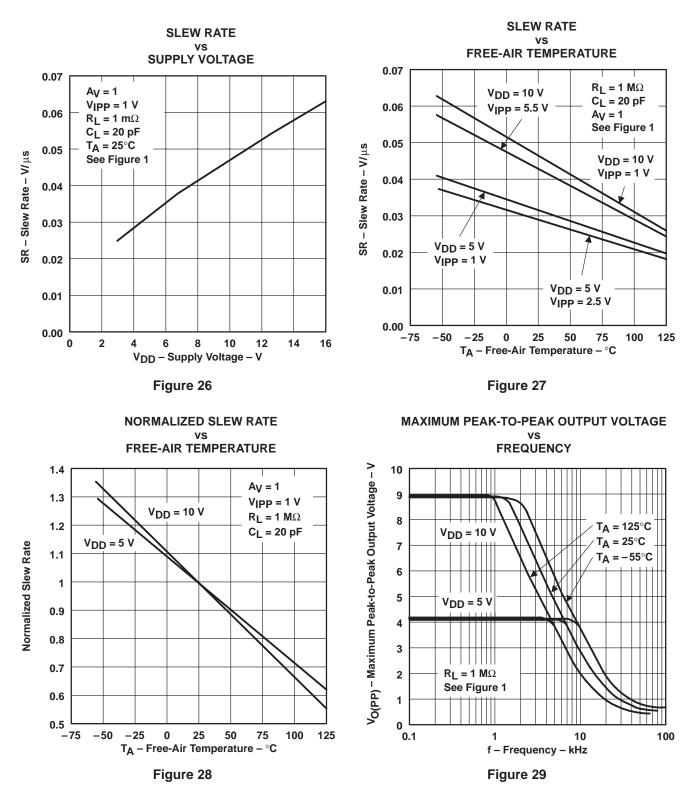
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**TYPICAL CHARACTERISTICS<sup>†</sup>** 



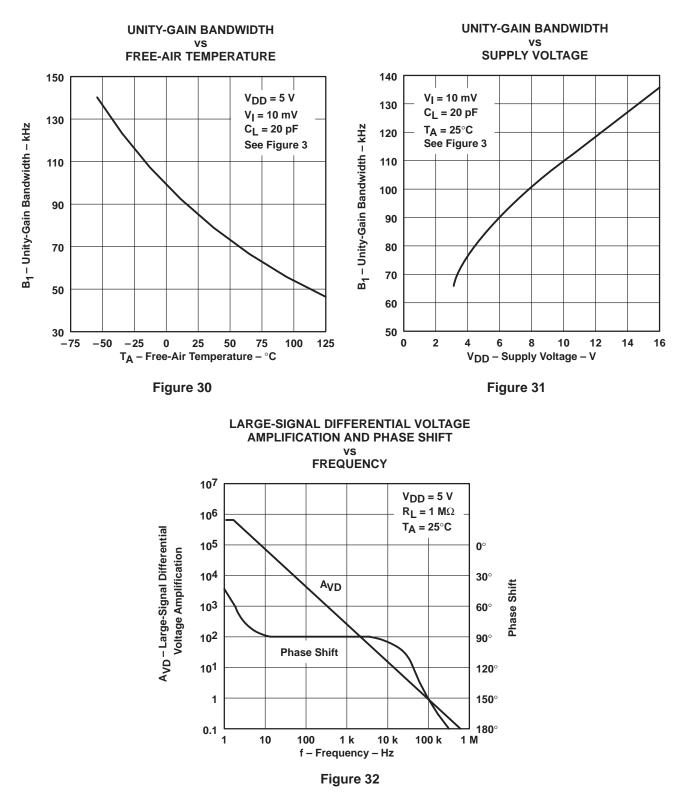
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### **TYPICAL CHARACTERISTICS<sup>†</sup>**



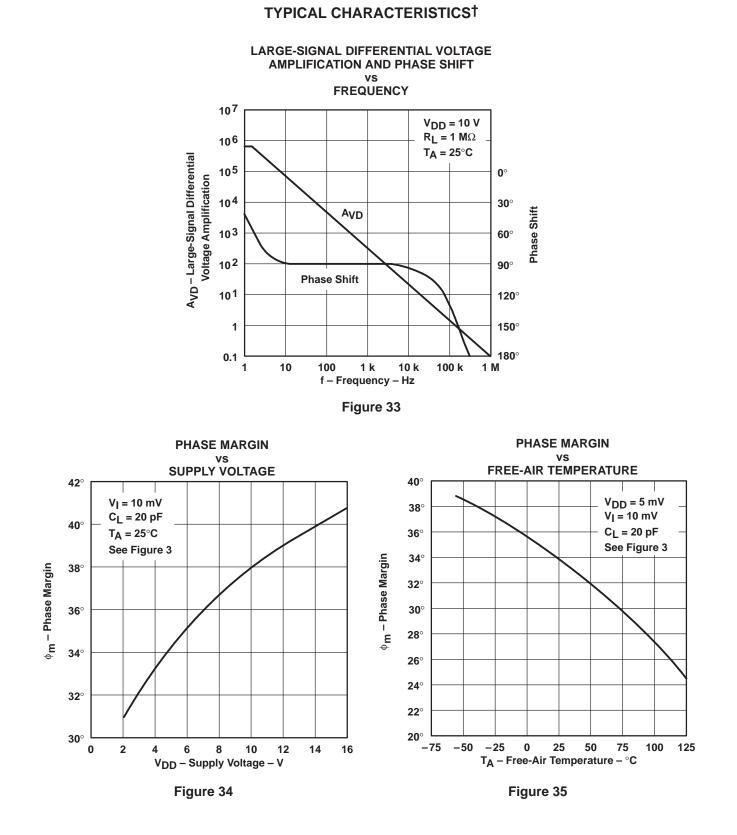
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**TYPICAL CHARACTERISTICS<sup>†</sup>** 



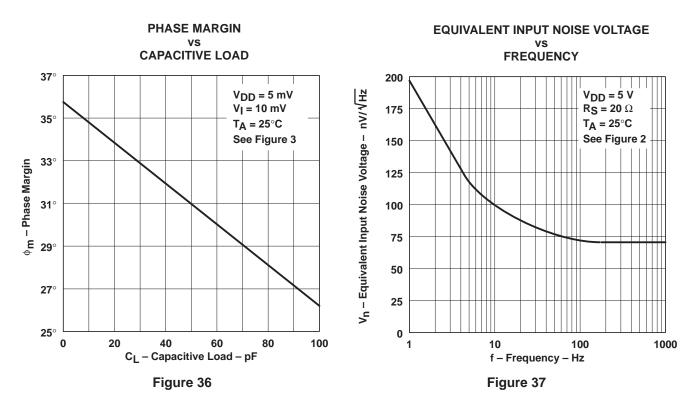
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#### **TYPICAL CHARACTERISTICS**





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### **APPLICATION INFORMATION**

#### single-supply operation

While the TLC27L4 and TLC27L9 perform well using dual power supplies (also called balanced or split supplies), the design is optimized for single-supply operation. This design includes an input common-mode voltage range that encompasses ground as well as an output voltage range that pulls down to ground. The supply voltage range extends down to 3 V (C-suffix types), thus allowing operation with supply levels commonly available for TTL and HCMOS; however, for maximum dynamic range, 16-V single-supply operation is recommended.

Many single-supply applications require that a voltage be applied to one input to establish a reference level that is above ground. A resistive voltage divider is usually sufficient to establish this reference level (see Figure 38). The low input bias current of the TLC27L4 and TLC27L9 permits the use of very large resistive values to implement the voltage divider, thus minimizing power consumption.

The TLC27L4 and TLC27L9 work well in conjunction with digital logic; however, when powering both linear devices and digital logic from the same power supply, the following precautions are recommended:

- 1. Power the linear devices from separate bypassed supply lines (see Figure 39); otherwise, the linear device supply rails can fluctuate due to voltage drops caused by high switching currents in the digital logic.
- 2. Use proper bypass techniques to reduce the probability of noise-induced errors. Single capacitive decoupling is often adequate; however, high-frequency applications may require RC decoupling.

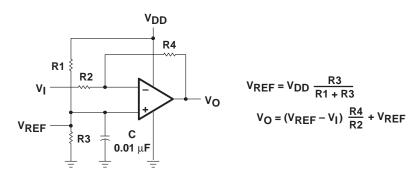
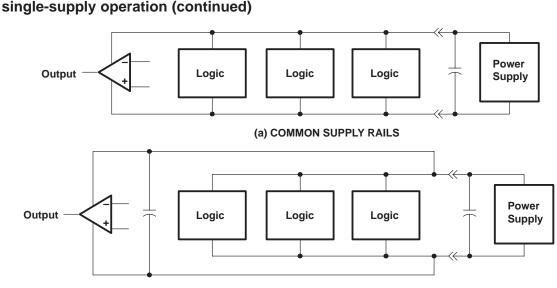


Figure 38. Inverting Amplifier With Voltage Reference



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#### **APPLICATION INFORMATION**



(b) SEPARATE BYPASSED SUPPLY RAILS (preferred)

Figure 39. Common Versus Separate Supply Rails

### input characteristics

The TLC27L4 and TLC27L9 are specified with a minimum and a maximum input voltage that, if exceeded at either input, could cause the device to malfunction. Exceeding this specified range is a common problem, especially in single-supply operation. Note that the lower range limit includes the negative rail, while the upper range limit is specified at  $V_{DD} - 1$  V at  $T_A = 25^{\circ}$ C and at  $V_{DD} - 1.5$  V at all other temperatures.

The use of the polysilicon-gate process and the careful input circuit design gives the TLC27L4 and TLC27L9 very good input offset voltage drift characteristics relative to conventional metal-gate processes. Offset voltage drift in CMOS devices is highly influenced by threshold voltage shifts caused by polarization of the phosphorus dopant implanted in the oxide. Placing the phosphorus dopant in a conductor (such as a polysilicon gate) alleviates the polarization problem, thus reducing threshold voltage shifts by more than an order of magnitude. The offset voltage drift with time has been calculated to be typically 0.1  $\mu$ V/month, including the first month of operation.

Because of the extremely high input impedance and resulting low bias current requirements, the TLC27L4 and TLC27L9 are well suited for low-level signal processing; however, leakage currents on printed circuit boards and sockets can easily exceed bias current requirements and cause a degradation in device performance. It is good practice to include guard rings around inputs (similar to those of Figure 4 in the Parameter Measurement Information section). These guards should be driven from a low-impedance source at the same voltage level as the common-mode input (see Figure 40).

The inputs of any unused amplifiers should be tied to ground to avoid possible oscillation.

#### noise performance

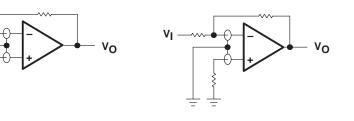
The noise specifications in operational amplifier circuits are greatly dependent on the current in the first-stage differential amplifier. The low input bias current requirements of the TLC27L4 and TLC27L9 result in a very low noise current, which is insignificant in most applications. This feature makes the devices especially favorable over bipolar devices when using values of circuit impedance greater than 50 k $\Omega$ , since bipolar devices exhibit greater noise currents.



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### **APPLICATION INFORMATION**

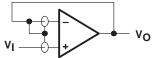
### noise performance (continued)



(a) NONINVERTING AMPLIFIER

#### (b) INVERTING AMPLIFIER

# Figure 40. Guard-Ring Schemes

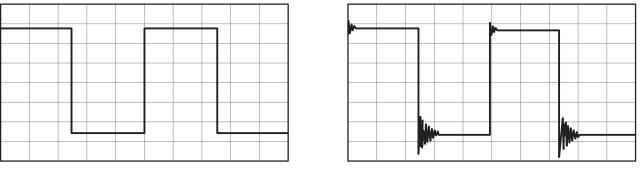


(c) UNITY-GAIN AMPLIFIER

#### output characteristics

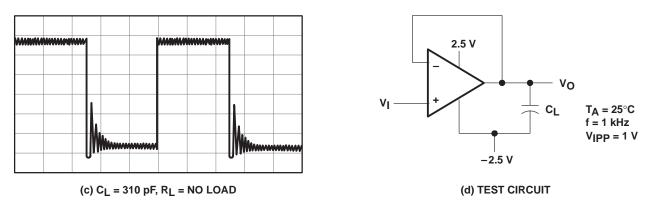
The output stage of the TLC27L4 and TLC27L9 is designed to sink and source relatively high amounts of current (see typical characteristics). If the output is subjected to a short-circuit condition, this high current capability can cause device damage under certain conditions. Output current capability increases with supply voltage.

All operating characteristics of the TLC27L4 and TLC27L9 were measured using a 20-pF load. The devices drive higher capacitive loads; however, as output load capacitance increases, the resulting response pole occurs at lower frequencies, thereby causing ringing, peaking, or even oscillation (see Figure 41). In many cases, adding a small amount of resistance in series with the load capacitance alleviates the problem.



(a)  $C_L = 20 \text{ pF}$ ,  $R_L = \text{NO LOAD}$ 









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#### **APPLICATION INFORMATION**

#### output characteristics (continued)

Although the TLC27L4 and TLC27L9 possess excellent high-level output voltage and current capability, methods for boosting this capability are available, if needed. The simplest method involves the use of a pullup resistor (Rb) connected from the output to the positive supply rail (see Figure 42). There are two disadvantages to the use of this circuit. First, the NMOS pulldown transistor N4 (see equivalent schematic) must sink a comparatively large amount of current. In this circuit, N4 behaves like a linear resistor with an on-resistance between approximately  $60 \Omega$  and  $180 \Omega$ , depending on how hard the operational amplifier input is driven. With very low values of R<sub>P</sub>, a voltage offset from 0 V at the output occurs. Second, pullup resistor R<sub>P</sub> acts as a drain load to N4 and the gain of the operational amplifier is reduced at output voltage levels where N5 is not supplying the output current.

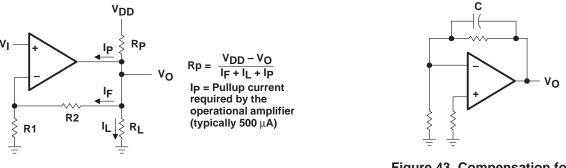


Figure 42. Resistive Pullup to Increase VOH



#### feedback

Operational amplifier circuits nearly always employ feedback, and since feedback is the first prerequisite for oscillation, some caution is appropriate. Most oscillation problems result from driving capacitive loads (discussed previously) and ignoring stray input capacitance. A small-value capacitor connected in parallel with the feedback resistor is an effective remedy (see Figure 43). The value of this capacitor is optimized empirically.

#### electrostatic discharge protection

The TLC27L4 and TLC27L9 incorporate an internal electrostatic discharge (ESD) protection circuit that prevents functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.2. Care should be exercised, however, when handling these devices, as exposure to ESD may result in the degradation of the device parametric performance. The protection circuit also causes the input bias currents to be temperature dependent and have the characteristics of a reverse-biased diode.

#### latch-up

Because CMOS devices are susceptible to latch-up due to their inherent parasitic thyristors, the TLC27L4 and TLC27L9 inputs and outputs were designed to withstand -100-mA surge currents without sustaining latch-up; however, techniques should be used to reduce the chance of latch-up whenever possible. Internal protection diodes should not, by design, be forward biased. Applied input and output voltage should not exceed the supply voltage by more than 300 mV. Care should be exercised when using capacitive coupling on pulse generators. Supply transients should be shunted by the use of decoupling capacitors (0.1  $\mu$ F typical) located across the supply rails as close to the device as possible.



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### **APPLICATION INFORMATION**

### latch-up (continued)

The current path established if latch-up occurs is usually between the positive supply rail and ground and can be triggered by surges on the supply lines and/or voltages on either the output or inputs that exceed the supply voltage. Once latch-up occurs, the current flow is limited only by the impedance of the power supply and the forward resistance of the parasitic thyristor and usually results in the destruction of the device. The chance of latch-up occurring increases with increasing temperature and supply voltages.

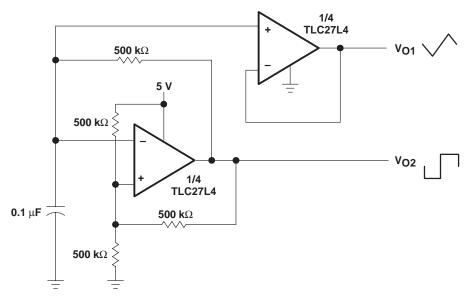
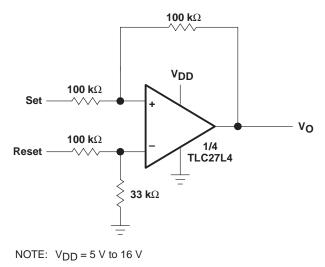


Figure 44. Multivibrator

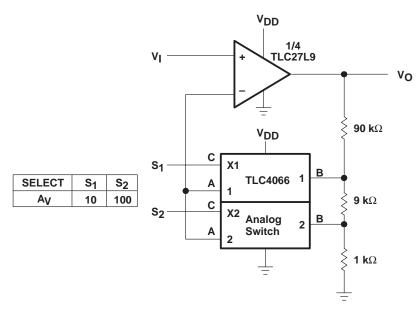


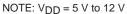




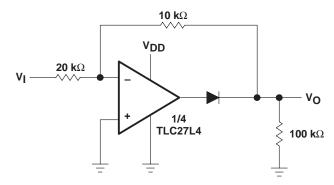
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#### **APPLICATION INFORMATION**

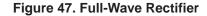




#### Figure 46. Amplifier With Digital Gain Selection



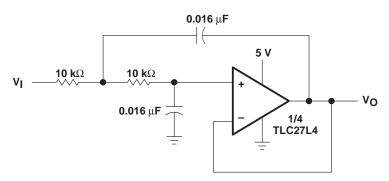
NOTE:  $V_{DD} = 5 V$  to 16 V





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### **APPLICATION INFORMATION**



NOTE: Normalized to F\_C = 1 kHz and R\_L = 10 k\Omega



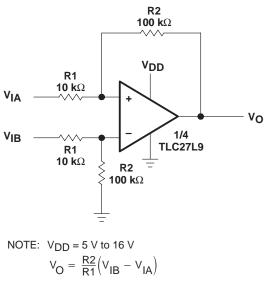


Figure 49. Difference Amplifier





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### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty		Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
TLC27L4ACD	(1) ACTIVE	SOIC	D	14	50	(2) Green (RoHS & no Sb/Br)	(6) CU NIPDAU	(3) Level-1-260C-UNLIM	0 to 70	(4/5) 27L4AC	Samples
TLC27L4ACDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27L4AC	Samples
TLC27L4ACDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27L4AC	Samples
TLC27L4ACDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27L4AC	Samples
TLC27L4ACN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27L4ACN	Samples
TLC27L4ACNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27L4ACN	Samples
TLC27L4AID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27L4AI	Samples
TLC27L4AIDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27L4AI	Samples
TLC27L4AIDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27L4AI	Samples
TLC27L4AIDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27L4AI	Samples
TLC27L4AIN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27L4AIN	Samples
TLC27L4BCD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27L4BC	Samples
TLC27L4BCDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27L4BC	Samples
TLC27L4BCDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27L4BC	Samples
TLC27L4BCN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27L4BCN	Samples
TLC27L4BID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27L4BI	Samples
TLC27L4BIDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27L4BI	Samples



# PACKAGE OPTION ADDENDUM

10-Jun-2014

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samp
	(1)				-	(2)	(6)	(3)		(4/5)	
TLC27L4BIDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27L4BI	Samp
TLC27L4BIDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27L4BI	Samp
TLC27L4BIN	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27L4BIN	Samj
TLC27L4CD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L4C	Sam
TLC27L4CDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L4C	Sam
TLC27L4CDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L4C	Sam
TLC27L4CDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L4C	Sam
TLC27L4CN	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27L4CN	Sam
TLC27L4CNSR	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L4	Sam
TLC27L4CPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P27L4C	Sam
TLC27L4CPWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P27L4C	Sam
TLC27L4CPWLE	OBSOLETE	TSSOP	PW	14		TBD	Call TI	Call TI	0 to 70		
TLC27L4CPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P27L4C	Sam
TLC27L4CPWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P27L4C	Sam
TLC27L4ID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC27L4I	Sam
TLC27L4IDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC27L4I	San
TLC27L4IDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC27L4I	San
TLC27L4IDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC27L4I	Sam



# PACKAGE OPTION ADDENDUM

10-Jun-2014

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	San
TLC27L4IN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27L4IN	Sar
TLC27L4INE4	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27L4IN	Sar
TLC27L4IPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	P27L4I	Sa
TLC27L4IPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	P27L4I	Sa
TLC27L4IPWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	P27L4I	Sa
TLC27L4MFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI	-55 to 125		
TLC27L4MJ	OBSOLETE	CDIP	J	14		TBD	Call TI	Call TI	-55 to 125		
TLC27L4MJB	OBSOLETE	CDIP	J	14		TBD	Call TI	Call TI	-55 to 125		
TLC27L9CD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L9C	Sa
TLC27L9CDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L9C	Sa
TLC27L9CDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L9C	Sa
TLC27L9CN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27L9CN	Sa
TLC27L9CNE4	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27L9CN	Sa
TLC27L9CNSR	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L9	Sa
TLC27L9ID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC27L9I	Sa
TLC27L9IDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC27L9I	Sa
TLC27L9IDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC27L9I	Sa
TLC27L9IN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27L9IN	Sa
TLC27L9MFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI	-55 to 125		
TLC27L9MJ	OBSOLETE	CDIP	J	14		TBD	Call TI	Call TI	-55 to 125		



10-Jun-2014

Orderable Device	Status	Package Type	•	Pins	•	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TLC27L9MJB	OBSOLETE	CDIP	J	14		TBD	Call TI	Call TI	-55 to 125		

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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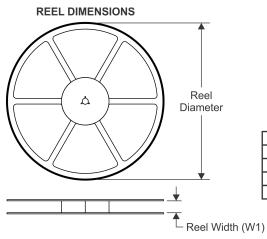
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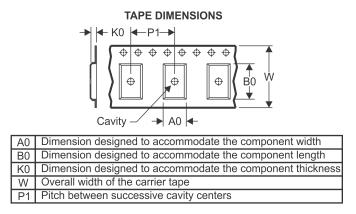
# PACKAGE MATERIALS INFORMATION

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### TAPE AND REEL INFORMATION





### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



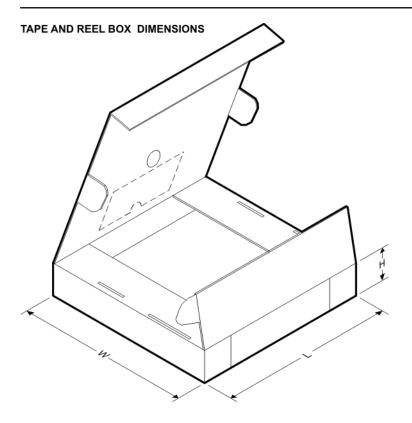
*All dimensions are nomina <b>Device</b>	Package			SPQ	Reel Diameter	Reel Width	A0	B0	K0	P1	W	Pin1 Quadrant
	Туре	Drawing			(mm)	W1 (mm)	(mm)	(mm)	(mm)	(mm)	(mm)	Quadrant
TLC27L4ACDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27L4ACDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27L4AIDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27L4BCDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27L4BIDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27L4CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27L4CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27L4CNSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
TLC27L4CPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TLC27L4IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27L4IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TLC27L9CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27L9CNSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
TLC27L9IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

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# PACKAGE MATERIALS INFORMATION

3-Jul-2013



All dimensions are nominal								
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
TLC27L4ACDR	SOIC	D	14	2500	367.0	367.0	38.0	
TLC27L4ACDR	SOIC	D	14	2500	333.2	345.9	28.6	
TLC27L4AIDR	SOIC	D	14	2500	367.0	367.0	38.0	
TLC27L4BCDR	SOIC	D	14	2500	367.0	367.0	38.0	
TLC27L4BIDR	SOIC	D	14	2500	367.0	367.0	38.0	
TLC27L4CDR	SOIC	D	14	2500	367.0	367.0	38.0	
TLC27L4CDR	SOIC	D	14	2500	333.2	345.9	28.6	
TLC27L4CNSR	SO	NS	14	2000	367.0	367.0	38.0	
TLC27L4CPWR	TSSOP	PW	14	2000	367.0	367.0	35.0	
TLC27L4IDR	SOIC	D	14	2500	367.0	367.0	38.0	
TLC27L4IPWR	TSSOP	PW	14	2000	367.0	367.0	35.0	
TLC27L9CDR	SOIC	D	14	2500	367.0	367.0	38.0	
TLC27L9CNSR	SO	NS	14	2000	367.0	367.0	38.0	
TLC27L9IDR	SOIC	D	14	2500	367.0	367.0	38.0	

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